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Interoffice Memorandum

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Date

January 31, 1992

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**Radiation Report on 54AC244DMQB
SMEX Part No. 5962-8755201RA
Control No. 1657**

A radiation evaluation was performed on the 54AC244DMQB to determine the total dose tolerance of these parts. A brief summary of the test results is provided below. For detailed information, refer to Tables I through IV and Figure 1.

The total dose testing was performed using a cobalt-60 gamma ray source. During the radiation testing, eight parts were irradiated under bias (see Figure 1 for bias configuration), and two parts were used as control samples. The total dose radiation steps were 10, 20, 30, 50, 75, and 100 krads*. After 100 krads, the parts were annealed under bias at +25°C for 216 hours. After this annealing, the parts were irradiated to 200 and 300 krads (cumulative). Finally, the parts were annealed under bias for 168 hours at 100°C. The dose rate was between 150 and 6,250 rads/hour, depending on the total dose level (see Table II for radiation schedule). After each radiation exposure and annealing treatment, the parts were electrically tested @ +25°C according to the test conditions and the specification limits listed in Table III. These tests included three functional tests at 10 MHz after each radiation and annealing step.

All parts passed all three functional tests on irradiation up to 300 krads and on subsequent high temperature annealing for 168 hours. Also, all parts stayed within specification limits for all parameters on irradiation up to 30 krads. However, after radiation exposure to 50 krads, one device was well in excess of the specified limit of 160 uA for ICCH, ICCL, and ICCZ (ICCH = 606 uA, ICCL = 345 uA, ICCZ = 284 uA) and another device marginally exceeded the limit for TCCH. Upon continued exposure to 100 krads, the same two devices suffered further degradation in the ICCH, ICCL, and ICCZ parameters. Readings were as high as 4.2 mA for ICCH and 3 mA for ICCL and ICCZ. After annealing for 216 hours at 25°C, these two parts recovered slightly, but were still exceeding the specified limits. After 200 krads of exposure, five devices were exceeding the limits for the same parameters with readings as high as 10 mA. In addition, two of these five parts were marginally exceeding the limit for TPZH1. After 300 krads seven devices were above the limit for the ICC parameters and six devices marginally surpassed the TPZH1 limit. After the 168 hour annealing at 100°C, the devices recovered very well with only one part marginally exceeding the limits for ICCH, ICCL, and ICCZ. All of the parts continued to marginally exceed the TPZH1 limit.

Table IV provides the mean and standard deviation values for each parameter after each radiation exposure and annealing treatment. It also provides a summary of the functional test results after each radiation/annealing step.

Any further details about this evaluation can be obtained upon request. If you have any questions, please call me at (301)731-8954.

In this report, the term rads is used as an abbreviation for rads (Si).

TABLE I. Part Information

Generic Part Number: 54AC244DMQB
SMEX Common Buy
Part Number: 5962-8755201RA
SMEX Common Buy
Control Number: 1657
Charge Number: C90358
Manufacturer: National Semiconductor Corp.
Lot Date Code: 9027A
Quantity Tested: 8
Serial Numbers of
Radiation Samples: 603, 604, 605, 606, 607, 608, 609, 610
Serial Number of
Control Sample: 601, 602
Part Function: OCTAL BUFFER
Part Technology: CMOS
Package Style: 20-pin DIP

TABLE II. Radiation Schedule for 54AC244DMQB

EVENTS	DATE
1) Initial (Pre-Irradiation) Electrical Measurements	07/17/91
2) 10 KRAD IRRADIATION (500 rads/hour)	12/09/91
POST 10 KRAD ELECTRICAL MEASUREMENT	12/12/91
3) 20 KRAD IRRADIATION (500 rads/hour)	12/12/91
POST 20 KRAD ELECTRICAL MEASUREMENT	12/13/91
4) 30 KRAD IRRADIATION (150 rads/hour)	12/13/91
POST 30 KRAD ELECTRICAL MEASUREMENT	12/17/91
5) 50 KRAD IRRADIATION (1,050 rads/hour)	12/17/91
POST 50 KRAD ELECTRICAL MEASUREMENT	12/18/91
6) 75 KRAD IRRADIATION (1,320 rads/hour)	12/18/91
POST 75 KRAD ELECTRICAL MEASUREMENT	12/19/91
7) 100 KRAD IRRADIATION (1,350 rads/hour)	12/19/91
POST 100 KRAD ELECTRICAL MEASUREMENT	12/20/91
8) 72 HOURS ANNEALING AT 25°C	12/20/91
POST 72 HOURS ELECTRICAL MEASUREMENT	12/23/91
9) 216 HOURS ANNEALING AT 25°C	12/20/91
POST 216 HOURS ELECTRICAL MEASUREMENT	12/30/91
10) 200 KRAD IRRADIATION (6,250 rads/hour)	12/30/91
POST 200 KRAD ELECTRICAL MEASUREMENT	12/31/91
11) 300 KRAD IRRADIATION (2,130 rads/hour)	12/31/91
POST 300 KRAD ELECTRICAL MEASUREMENT	01/02/92
12) 168 HOURS ANNEALING AT +100°C	01/02/92
POST 168 HOURS AT +100°C ELECTRICAL MEASUREMENTS	01/10/92

Notes:

- All parts were radiated under bias at the cobalt-60 gamma ray facility at GSFC.
- All electrical measurements were performed off-site at +25°C.
- All Annealing steps were performed under bias.

Table III. Electrical Characteristics of 54AC244DMQB

TESTS PERFORMED								
PARAMETER	V _{CC}	V _{IL}	V _{IR}	CONDITIONS	PINS	LIMITS: -55C TO +125C		
FUNC 1	5.0V	0.0V	2.0V	V _{FBW} = 10MHz	ALL I/O	V _{OH} >1.00V, V _{OL} <1.00V		
FUNC 2	5.5V	0.0V	2.5V	V _{FBW} = 10MHz	ALL I/O	V _{OH} >1.00V, V _{OL} <1.00V		
FUNC 3	5.5V	0.0V	2.5V	V _{FBW} = 10MHz	ALL I/O	V _{OH} >1.00V, V _{OL} <1.00V		
V _{OH1}	5.0V	INPUTS AT 0.90V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	2.90V MIN		
V _{OH2}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	4.40V MIN		
V _{OH3}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	5.40V MIN		
V _{OH4}	5.0V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -25mA	2.40V MIN		
V _{OH5}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -25mA	3.70V MIN		
V _{OH6}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	4.70V MIN		
V _{OH7}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	5.85V MIN		
V _{OH8}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	6.1V MAX		
V _{OL1}	5.0V	INPUTS AT 0.40V AND 1.55V	AND 2.10V	EACH	OUTPUT AT -50mA	0.1V MAX		
V _{OL2}	4.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	0.1V MAX		
V _{OL3}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -12mA	0.5V MAX		
V _{OL4}	5.0V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -25mA	0.5V MAX		
V _{OL5}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -25mA	0.5V MAX		
V _{OL6}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	1.65V MAX		
V _{OL7}	5.5V	INPUTS AT 1.55V AND 2.10V	AND 3.15V	EACH	OUTPUT AT -50mA	1.70V TO OUR		
I _{OL1}	5.5V	EACH OUTPUT TESTED AT V _{IN} =0.0V				0.00A TO 100A		
I _{OL2}	5.5V	EACH OUTPUT TESTED AT V _{IN} =5.5V				-1.03A TO 100A		
I _{OL3}	5.5V	EACH INPUT TESTED AT V _{IN} =5.5V				0.00A TO 100A		
I _{ICN}	5.5V	INPUTS AT 0.0V				160.0UA MAX		
I _{ICL}	5.5V	INPUTS AT 0.0V				160.0UA MAX		
I _{ICL}	5.5V	INPUTS AT 5.5V AND 0.0V				160.0UA MAX		
PARAMETER	V _{CC}	V _{IL}	V _{IR}	CONDITIONS	PINS	LIMITS: 25C		
TPLH1	5.0V	5.0V	3.0V	10H =+10.0MA OUTPUTS 10L =+10.0MA VCOMP= +1.5V		>1.0NS <10.0NS		
TPLH2	4.5V	4.0V	4.5V	=+10.0MA OUTPUTS 10L = +10.0MA VCOMP= +2.25V		>1.0NS <8.0NS		
TPLH3	5.0V	5.0V	3.0V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= +1.5V		>1.0NS <11.0NS		
TPLH2	4.5V	4.0V	4.5V	=+10.0MA OUTPUTS 10L = +10.0MA VCOMP= +2.25V		>1.0NS <8.0NS		
TPLL1	5.0V	5.0V	3.0V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= -0.3V		>1.0NS <11.0NS		
TPLL2	4.5V	4.0V	4.5V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= -0.45V		>1.0NS <9.0NS		
TPLL3	5.0V	5.0V	3.0V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= -1.5V		>1.0NS <11.0NS		
TPLL7	4.5V	4.0V	4.5V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= -2.25V		>1.0NS <8.0NS		
TPLH1	5.0V	5.0V	3.0V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= VCC-0.3V		>1.0NS <10.0NS		
TPLH2	4.5V	4.0V	4.5V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= VCC-0.45V		>1.0NS <8.0NS		
TPLH3	5.0V	5.0V	3.0V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= +1.5V		>1.0NS <9.0NS		
TPLH2	4.5V	4.0V	4.5V	10H =+10.0MA OUTPUTS 10L = +10.0MA VCOMP= +2.25V		>1.0NS <7.5NS		

TABLE IV: Summary of Electrical Measurements After Total Dose Exposures and Annealing for 54AC244DMQB 1/2/3/

Parameters	Total Dose Exposure (TDE) (krads)												Anneal (TDE) (krads)			Anneal				
	0			10			30			50			75			100			216 hour @ 25°C	
	spec limits @ 25°C	min	max	mean	sd	mean	sd	mean	sd	Pass	Pass									
FONC1 @ 10 MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	
FONC2 @ 10 MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	
FONC3 @ 10 MHz	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	Pass	
VCH1_3.0V_V	2.3	5.5	2.99	0	3.00	0	3.00	0.01	2.99	0	2.99	0	2.99	0	2.99	0	2.99	0	2.99	0
VCH2_4.5V_V	4.4	5.5	4.49	0	4.49	0	4.49	0	4.49	0	4.49	0	4.49	0	4.49	0	4.49	0	4.49	0
VCH3_5.5V_V	5.4	5.5	5.49	0	5.49	0	5.49	0	5.49	0	5.49	0	5.49	0	5.49	0	5.49	0	5.49	0
VCH4_3.0V_V	2.4	5.5	2.93	0.01	2.93	0	2.92	0	2.92	0	2.92	0	2.92	0	2.92	0	2.92	0	2.92	0
VCH5_4.5V_V	3.7	5.5	4.16	2.01	4.18	0.01	4.18	0.01	4.18	0.01	4.17	0.01	4.17	0.01	4.16	0.01	4.16	0.01	4.16	0.01
VCH6_5.5V_V	4.7	5.5	5.21	0.01	5.22	0.01	5.22	0.01	5.22	0.01	5.21	0.01	5.21	0.01	5.20	0.01	5.20	0.01	5.20	0.01
VCH7_5.5V_V	3.85	5.5	4.89	0.02	4.90	0.02	4.90	0.02	4.90	0.02	4.89	0.02	4.89	0.02	4.87	0.02	4.87	0.02	4.86	0.02
VCL1_3.0V_V	0	0.1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
VCL2_4.5V_V	0	0.1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
VOL3_5.5V_V	0	0.1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
VOL4_3.0V_V	0	0.5	0.44	0.01	0.44	0	0.44	0	0.44	0	0.44	0	0.44	0	0.44	0	0.44	0	0.44	0
VOL5_4.5V_V	0	0.5	0.21	0.01	0.20	0.01	0.20	0.01	0.20	0.01	0.20	0.01	0.20	0.01	0.20	0.01	0.20	0.01	0.20	0.01
VOL6_5.5V_V	0	0.5	0.18	0.01	0.18	0.01	0.18	0.01	0.18	0.01	0.18	0.01	0.18	0.01	0.18	0.01	0.18	0.01	0.18	0.01
VOL7_5.5V_V	0	1.65	0.39	0.02	0.38	0.01	0.38	0.01	0.38	0.01	0.38	0.01	0.38	0.01	0.38	0.01	0.38	0.01	0.38	0.01
IOL2L_UA	-10	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
IOL2H_UA	0	10	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
TIL_UA	-1.0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
III_UA	0	1.0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
ICCH_UA	0	160	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
ICCL_UA	0	160	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
ICZ2_UA	0	160	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

TABLE IV (CONTINUED) : Summary of Electrical Measurements After
Total Dose Exposures and Annealing for S4AC244DMQB 1/2/3¹

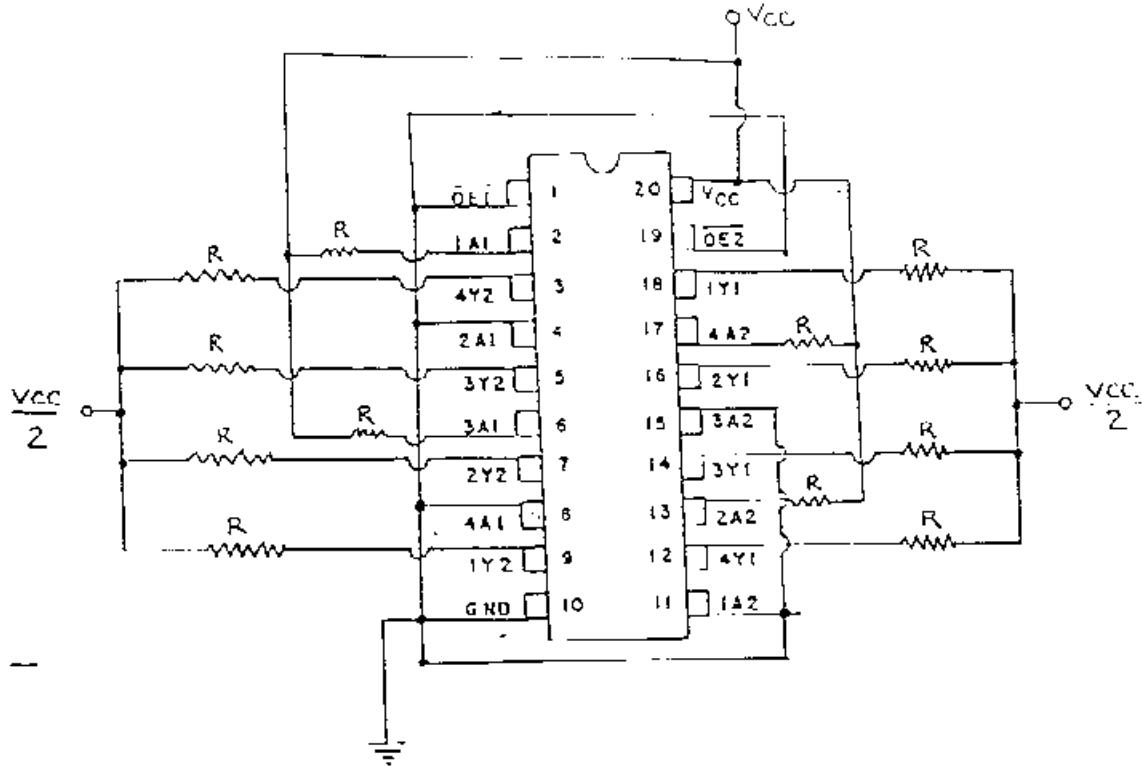
Parameters	Spec Limits @ 25°C	Total Dose Exposure (TDE) (krads)												Anneal			'TDE' (krads)			Anneal			
		0 (Pre-Rad)			10			30			50			75			100			216 hour @ 25°C			
		mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd	mean	sd
TPEL1	rs	1.0	10.5	4.87	0.41	6.58	0.67	7.56	0.65	7.61	0.66	7.62	0.64	7.50	0.71	7.61	0.68	7.67	0.69	7.61	0.82		
TPEL2	rs	1.0	8.0	4.56	0.36	6.29	0.71	7.29	0.71	7.35	0.74	7.36	0.74	7.24	0.77	7.33	0.77	7.40	0.81	7.38	0.91		
TPL1	rs	1.0	11.0	5.83	0.38	6.51	1.04	7.51	1.01	7.49	1.06	7.54	1.11	7.55	1.14	7.46	1.27	7.64	1.44	7.82	1.91	7.80	1.40
TPL2	rs	1.0	8.5	5.26	0.37	5.91	0.85	6.89	0.78	6.04	0.52	6.85	0.82	6.83	0.82	6.77	0.75	6.70	0.79	6.68	0.86	6.76	0.77
TPL2	rs	1.0	11.0	6.47	0.32	7.08	0.22	8.03	0.21	8.02	0.19	7.94	0.22	7.98	0.22	7.61	0.25	7.61	0.24	7.61	0.26	7.39	0.27
TPL2	rs	1.0	9.0	7.05	0.34	7.78	0.24	8.72	0.23	8.67	0.24	8.65	0.25	8.60	0.25	8.31	0.29	8.28	0.29	8.26	0.31	8.06	0.26
TPZ1	rs	1.0	11.0	7.26	0.40	9.59	0.28	10.54	0.29	10.49	0.30	10.47	0.29	10.51	0.27	10.23	0.31	10.17	0.35	10.14	0.38	10.77	0.41
TPZ2	rs	1.0	8.5	5.4	0.32	6.09	0.20	9.05	0.20	9.02	0.22	9.04	0.21	9.09	0.20	8.76	0.24	8.77	0.24	8.75	0.23	8.84	0.23
TPZ2	rs	1.0	10.0	3.72	0.18	4.65	0.12	5.58	0.12	5.56	0.13	5.47	0.16	5.49	0.16	5.72	0.21	5.57	0.23	5.43	0.23	5.56	0.21
TPHZ1	rs	1.0	8.5	4.87	0.21	5.87	0.14	6.78	0.13	6.73	0.14	6.70	0.15	6.72	0.13	6.96	0.16	6.93	0.19	6.74	0.18	6.86	0.17
TPHZ1	rs	1.0	9.5	7.85	0.49	8.70	0.39	9.82	0.41	9.92	0.44	10.05	0.47	10.24	0.48	10.47	0.50	10.87	0.54	11.12	0.51	11.44	0.43
TPHZ2	rs	1.0	7.5	5.42	0.46	7.03	0.29	8.07	0.30	8.10	0.32	8.15	0.33	8.29	0.33	8.52	0.38	8.75	0.40	8.89	0.41	9.03	0.35

1/ These statistics do not include the control samples which remained constant throughout testing.

2/ The statistics for the post 20 krad and 72 hour annealing steps are available upon request.

3/ The statistical data for the 50 krad step does not include S/N 604 and 605 for the TPLZ1 and TEHZ- parameters due to equipment related problems in gathering data for those parts. The 300 krad step does not include S/N 605 for the TEHZ2 parameter for the same reason.

Figure 1. Radiation Bias Circuit for 54AC244DMQB



All RESISTORS : 1 K ohm $\pm 5\%$, $\frac{1}{4}$ W

V_{CC} shall be 5.0 V $\pm 10\%$; $\frac{V_{CC}}{2} = 2.5 V \pm 10\%$

T_A = 25 °C